

Application No. 10/748,078

Amendments to the Specification:

Please replace paragraph [0001] with the following amended paragraph:

Cross-Reference to Related Applications

[0001] The following patent applications, herein incorporated by reference, are related to the present application: PCT Application Serial No. PCT/US00/33786, filed on December 13, 2000, entitled "Ion Implantation Ion Source, System and Method", inventor Thomas N. Hersky; PCT Application No. PCT/US01/18822, filed June 12, 2001, entitled "Ion Implantation with High Brightness, Low Emissance Ion Source, Acceleration Declaration", inventor Thomas N. Hersky; PCT Application Serial No. PCT/US02/03258, filed February 5, 2002, entitled, "Ion Source for Ion Implantation", inventor Thomas N. Hersky and U.S. Application No. 09/736,097, filed December 13, 2000, entitled "Electron Beam Ion Source with Integral Low Temperature Vaporizer" inventor Thomas N. Hersky. This is a continuation of prior application number 10/183,768, filed June 26, 2002, now U.S. Patent No. 6,686,595, which is hereby incorporated herein by reference in its entirety.